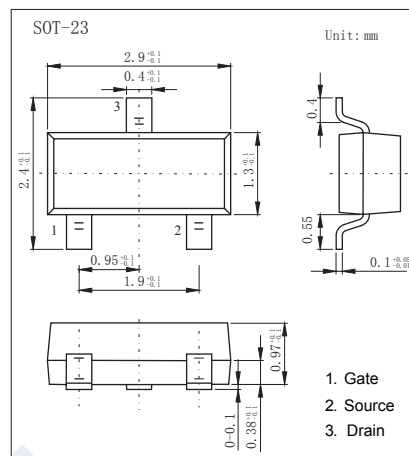
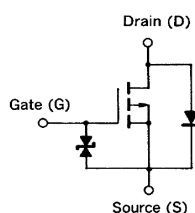


P-Channel MOSFET

2SJ209

■ Features

- $V_{DS} (V) \approx -100V$
- $I_D \approx -0.1 A$
- $R_{DS(ON)} < 60 \Omega$ ($V_{GS} \approx -10V$)
- $R_{DS(ON)} < 100 \Omega$ ($V_{GS} \approx -4V$)



■ Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	-100	V
Gate-Source Voltage	V_{GS}	± 16	
Continuous Drain Current	I_D	-0.1	A
Pulsed Drain Current (Note.1)	I_{DM}	-0.2	
Power Dissipation	P_D	0.2	W
Junction Temperature	T_J	150	$^\circ C$
Junction Storage Temperature Range	T_{stg}	-55 to 150	

Note.1: $PW \leq 10$ ms, duty cycle $\leq 50\%$

■ Electrical Characteristics $T_a = 25^\circ C$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	V_{DSS}	$I_D = -250 \mu A$, $V_{GS} = 0V$	-100			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} \approx -100V$, $V_{GS} = 0V$			-1	μA
Gate-Body leakage current	I_{GSS}	$V_{DS} = 0V$, $V_{GS} = \pm 16V$			± 10	μA
Gate to Source Cutoff Voltage	$V_{GS(off)}$	$V_{GS} = -5V$, $I_D = -1mA$	-1.5		-2.5	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS} = -10V$, $I_D = -10mA$			60	Ω
		$V_{GS} = -4V$, $I_D = -10mA$			100	
Forward Transconductance	g_{FS}	$V_{DS} = -5V$, $I_D = -10mA$	15	22		mS
Input Capacitance	C_{iss}	$V_{GS} = 0V$, $V_{DS} = -5V$, $f = 1MHz$		17		pF
Output Capacitance	C_{oss}			9		
Reverse Transfer Capacitance	C_{rss}			1		
Turn-On DelayTime	$t_{d(on)}$	$V_{GS(on)} = -4V$, $I_D = -10mA$, $R_L = 500 \Omega$, $R_G = 10 \Omega$, $V_{DD} = -5V$,		45		ns
Turn-On Rise Time	t_r			75		
Turn-Off DelayTime	$t_{d(off)}$			25		
Turn-Off Fall Time	t_f			80		

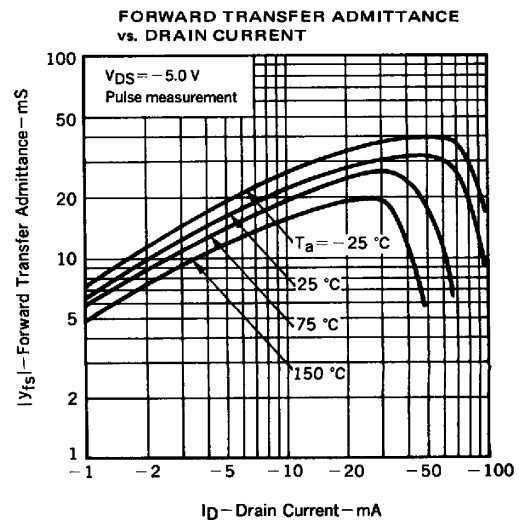
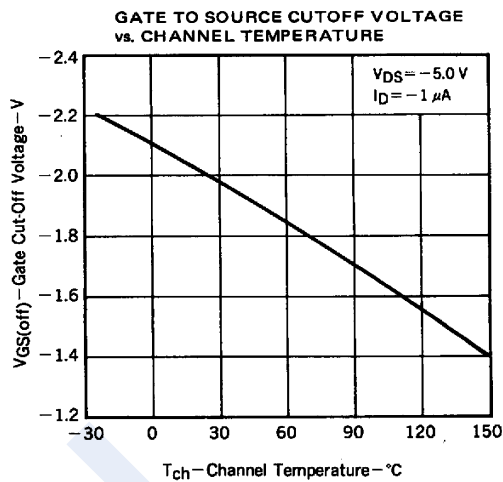
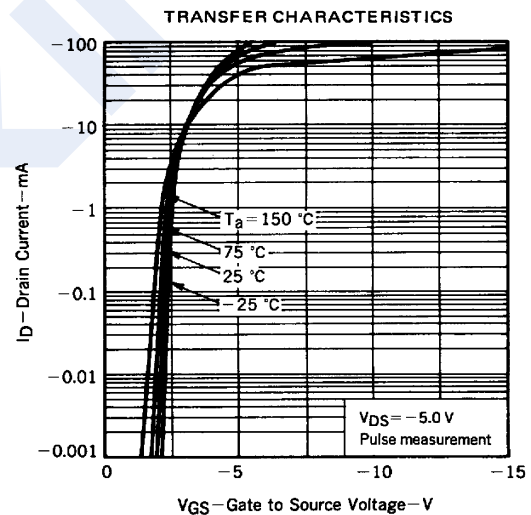
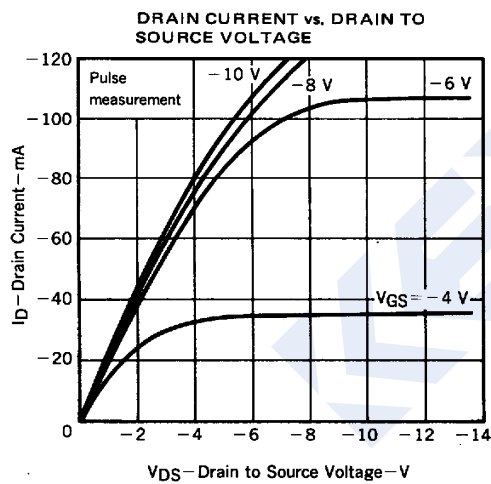
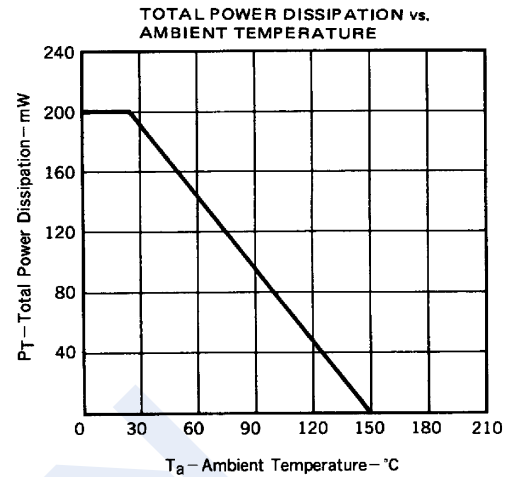
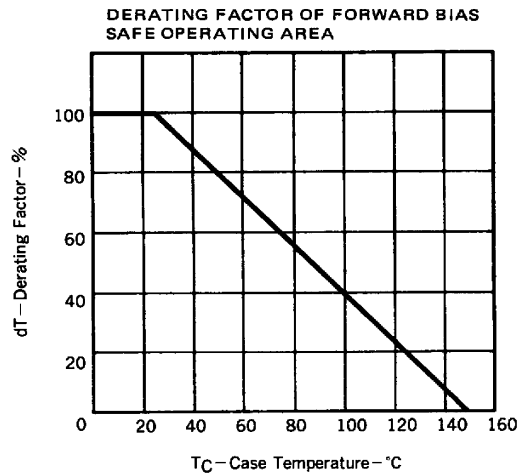
■ Marking

Marking	H17
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P-Channel MOSFET

2SJ209

■ Typical Characteristics



P-Channel MOSFET

2SJ209

■ Typical Characteristics

